







SN75HVD05, SN75HVD06, SN75HVD07 SN65HVD05, SN65HVD06, SN65HVD07 SLLS533F - MAY 2002 - REVISED MARCH 2023

SN65HVD0x, SN75HVD0x High Output RS-485 Transceivers

1 Features

- Minimum differential output voltage of 2.5 V Into a 54-Ω load
- Open-circuit, short-circuit, and idle-bus failsafe receiver
- 1/8th Unit-load option available (Up to 256 nodes on the bus)
- Bus-pin ESD protection exceeds 16 kV HBM
- Driver output slew rate control options
- Electrically compatible with ANSI TIA/EIA-485-A standard
- Low-current standby mode: 1 µA typical
- Glitch-free power-up and power-down protection for hot-plugging applications
- Pin compatible with industry standard SN75176

2 Applications

- Data transmission over long or lossy lines or electrically noisy environments
- Profibus line interface
- Industrial process control networks
- Point-of-sale (POS) networks
- Electric utility metering
- **Building automation**
- Digital motor control

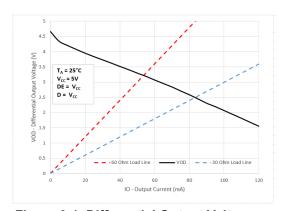


Figure 3-1. Differential Output Voltage vs **Differential Output Current**

3 Description

The SN65HVD05. SN75HVD05. SN65HVD06, SN65HVD07, SN75HVD06, and SN75HVD07 combine a 3-state differential line driver and differential line receiver. They are designed for balanced data transmission and interoperate with ANSI TIA/EIA-485-A and ISO 8482E standardcompliant devices. The driver is designed to provide a differential output voltage greater than that required by these standards for increased noise margin. The drivers and receivers have active-high and activelow enables respectively, which can be externally connected together to function as direction control.

The driver differential outputs and receiver differential inputs connect internally to form a differential input/ output (I/O) bus port that is designed to offer minimum loading to the bus whenever the driver is disabled or not powered. These devices feature wide positive and negative common-mode voltage ranges, making them suitable for party-line applications.

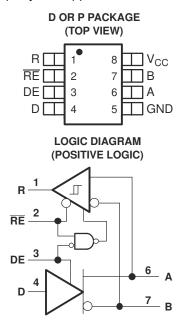




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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision E (August 2009) to Revision F (March 2023)				
Deleted the Ordering Information table	1			
Added the Thermal Information table	4			
Changed the Typical Characteristics	9			
Changes from Revision D (July 2006) to Revision E (August 2009)	Page			
Added IDLE Bus to the Receivers Function Table	16			

Added the Receiver Failsafe paragraph......16



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range unless otherwise noted(1) (2)

			SN65HVD05, SN65HVD06, SN65HVD07 SN75HVD05, SN75HVD06, SN75HVD07	
Supply voltage range, V ₀	DC		-0.3 V to 6 V	
Voltage range at A or B		–9 V to 14 V		
Input voltage range at D,	DE, R or RE	-0.5 V to V _{CC} + 0.5 V		
Voltage input range, tran	sient pulse, A and B, through 100	–50 V to 50 V		
Receiver output current,	I ₀		-11 mA to 11mA	
	Human hady madal(3)	A, B, and GND	16 kV	
Electrostatic discharge	Human body model ⁽³⁾	All pins	4 kV	
	Charged-device model ⁽⁴⁾	All pins	1 kV	
Continuous total power dissipation		See Dissipation Rating Table		

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under" recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- (2) All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.
- (3) Tested in accordance with JEDEC Standard 22, Test Method A114-A.
- (4) Tested in accordance with JEDEC Standard 22, Test Method C101.

5.2 Recommended Operating Conditions

		MIN	NOM MAX	UNIT
Supply voltage, V _{CC}		4.5	5.5	V
Voltage at any bus terminal (separatel	y or common mode) V _I or V _{IC}	-7 ⁽¹⁾	12	V
High-level input voltage, V _{IH}	D, DE, RE	2		V
Low-level input voltage, V _{IL}	D, DE, RE		0.8	V
Differential input voltage, V _{ID} (see Fig	ure 6-7)	-12	12	V
High-level output current, I _{OH}	Driver	-100		
	Receiver	-8	,	mA
	Driver		100	
Low-level output current, I _{OL}	Receiver		8	mA
	SN65HVD05			
	SN65HVD06	-40	85	°C
Operating free-air temperature, T _A	SN65HVD07			
	SN75HVD05		,	
	SN75HVD06	0	70	°C
	SN75HVD07			

⁽¹⁾ The algebraic convention, in which the least positive (most negative) limit is designated as minimum is used in this data sheet.



5.3 Thermal Information

	THERMAL METRIC ⁽¹⁾	D (SOIC) SN65 Variation	D (SOIC) SN75 Variation	P (PDIP)	UNIT
		8 PINS	8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	116.7	175.4	125	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	56.3	53.6	34.9	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	63.4	45.1	23.7	°C/W
ΨЈТ	Junction-to-top characterization parameter	8.8	10.1	12.1	°C/W
ΨЈВ	Junction-to-board characterization parameter	62.6	44.4	23.6	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

5.4 Package Dissipation Ratings

(See Figure 5-1 and Figure 5-2)

PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR ⁽¹⁾ ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING
D ⁽²⁾	710 mW	5.7 mW/°C	455 mW	369 mW
D ⁽³⁾	1282 mW	10.3 mW/°C	821 mW	667 mW
Р	1000 mW	8.0 m W/°C	640 mW	520 mW

- (1) This is the inverse of the junction-to-ambient thermal resistance when board-mounted and with no air flow.
- (2) Tested in accordance with the Low-K thermal metric definitions of EIA/JESD51-3
- (3) Tested in accordance with the High-K thermal metric definitions of EIA/JESD51-7



5.5 Driver Electrical Characteristics

PARAMETER		TEST CONDITIONS		MIN	TYP ⁽¹⁾	MAX	UNIT	
V _{IK}	Input clamp voltage		I _I = -18 mA		-1.5			V
			No Load				V_{CC}	
$ V_{OD} $	Differential output voltage		$R_L = 54 \Omega$, See Figure	e 6-4	2.5			V
			$V_{\text{test}} = -7 \text{ V to } 12 \text{ V, } 5$	See Figure 6-2	2.2			
Δ V _{OD}	Change in magnitude of differential voltage	output	See Figure 6-4 and F	igure 6-2	-0.2		0.2	V
V _{OC(SS)}	Steady-state common-mode output	voltage			2.2		3.3	V
$\Delta V_{OC(SS)}$	Change in steady-state common-moutput voltage	Change in steady-state common-mode output voltage		See Figure 6-3			0.1	V
		HVD05				600		
V _{OC(PP)} Peak-to-peak common-mode output voltage		HVD06	See Figure 6-3		500		mV	
		HVD07				900		
I _{OZ}	High-impedance output current		See receiver input cu					
l _l	Input current	D			-100		0	μΑ
"	input current	DE		0		100	μΛ	
Ios	Short-circuit output current		$-7 \text{ V} \leq \text{V}_{\text{O}} \leq 12 \text{ V}$		-250		250	mA
$C_{(diff)}$	Differential output capacitance		$V_{ID} = 0.4 \sin (4E6\pi t)$	+ 0.5 V, DE at 0 V		16		pF
			$\overline{\text{RE}}$ at V_{CC} , D and DE at V_{CC} , No load	Receiver disabled and driver enabled		9	15	mA
I _{cc}	Supply current		RE at V _{CC} , D at V _{CC} DE at 0 V, No load	Receiver disabled and driver disabled (standby)		1	5	μA
			RE at 0 V, D and DE at V _{CC} , No load	Receiver enabled and driver enabled		9	15	mA

⁽¹⁾ All typical values are at 25°C and with a 5-V supply.



5.6 Driver Switching Characteristics

	PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
		HVD05			6.5	11	
t _{PLH}	Propagation delay time, low-to-high-level output	HVD06	_		27	40	ns
		HVD07			250	400	
		HVD05			6.5	11	
t _{PHL}	Propagation delay time, high-to-low-level output	HVD06			27	40	ns
		HVD07			250	400	
		HVD05		2.7	3.6	6	
t _r	Differential output signal rise time	HVD06		18	28	55	ns
		HVD07	$R_L = 54 \Omega, C_L = 50 pF,$	150	300	450	
		HVD05	See Figure 6-4	2.7	3.6	6	
t _f	Differential output signal fall time	HVD06		18	28	55	ns
		HVD07		150	300	450	
		HVD05				2	
t _{sk(p)}	Pulse skew (t _{PHL} - t _{PLH})	HVD06				2.5	ns
		HVD07				10	
		HVD05				3.5	
t _{sk(pp)} (2)	Part-to-part skew	HVD06	_			14	ns
		HVD07				100	
		HVD05				25	
t _{PZH1}	Propagation delay time, high-impedance-to-high- level output	HVD06				45	ns
	level output	HVD07	\overline{RE} at 0 V, $R_L = 110 \Omega$,				
		HVD05	See Figure 6-5		25		
t_{PHZ}	Propagation delay time, high-level-to-high- impedance output	HVD06		60		60	ns
	impedance output	HVD07		250			
		HVD05				15	
t _{PZL1}	Propagation delay time, high-impedance-to-low-level output	HVD06				45	ns
	output	HVD07	\overline{RE} at 0 V, R _L = 110 Ω ,			200	
		HVD05	See Figure 6-6			14	
t_{PLZ}	Propagation delay time, low-level-to-high-impedance output	HVD06				90	ns
	output	HVD07				550	
t _{PZH2}	Propagation delay time, standby-to-high-level output	ı	R_L = 110 Ω , \overline{RE} at 3 V, See Figure 6-5			6	μs
t _{PZL2}	Propagation delay time, standby-to-low-level output		$R_L = 110 \Omega$, \overline{RE} at 3 V, See Figure 6-6			6	μs

⁽¹⁾ All typical values are at 25°C and with a 5-V supply.

⁽²⁾ $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.



5.7 Receiver Electrical Characteristics

	PARAMETER		TEST CONDITIONS			MIN	TYP ⁽¹⁾	MAX	UNIT
V _{IT+}	Positive-going inputhreshold voltage	ut	I _O = -8 mA					-0.01	V
V _{IT-}	Negative-going inp threshold voltage	out	I _O = 8 mA			-0.2			V
V _{hys}	Hysteresis voltage (V _{IT+} - V _{IT-})						35		mV
V _{IK}	Enable-input clam	o voltage	I _I = -18 mA			-1.5			V
V _{OH}	High-level output v	oltage	V _{ID} = 200 mV,	$I_{OH} = -8 \text{ mA},$	See Figure 6-7	4			V
V _{OL}	Low-level output v	oltage	V _{ID} = -200 mV,	I _{OL} = 8 mA,	See Figure 6-7			0.4	V
I _{OZ}	High-impedance-s output current	tate	V _O = 0 or V _{CC}	RE at V _{CC}		-1		1	μΑ
				V _A or V _B = 12 V			0.23	0.5	
		HVD05	Other inputat 0 V	V_A or $V_B = 12 V$,	V _{CC} = 0 V		0.3	0.5	A
		HVD05	Other inputation	V_A or $V_B = -7 \text{ V}$		-0.4	0.13		mA
	Bus input current			V_A or $V_B = -7 V$,	V _{CC} = 0 V	-0.4	0.15		
I _I	Bus input current			V_A or $V_B = 12 V$			0.06	0.1	
		HVD06	Other inputat 0 V	V_A or $V_B = 12 V$,	V _{CC} = 0 V		0.08	0.13	mA
		HVD07	Other inputation	V_A or $V_B = -7 V$		-0.1	0.05		ША
				V_A or $V_B = -7 V$,	$V_{CC} = 0 V$	-0.05	0.03		
I _{IH}	High-level input cu	rrent, RE	V _{IH} = 2 V			-60	26.4		μΑ
I _{IL}	Low-level input cu	rrent, RE	V _{IL} = 0.8 V			-60	27.4		μΑ
C _(diff)	Differential input capacitance		V _I = 0.4 sin (4E6πt) + 0.	5 V, DE at 0 V			16		pF
	cc Supply current		RE at 0 V, D and DE at 0 V, No load	Receiver enabled an	d driver disabled		5	10	mA
I _{CC}			RE at V _{CC} , DE at 0 V, D at V _{CC} , No load	Receiver disabled ar (standby)	nd driver disabled		1	5	μΑ
			RE at 0 V, D and DE at V _{CC} , No load	Receiver enabled an	d driver enabled		9	15	mA

⁽¹⁾ All typical values are at 25°C and with a 5-V supply.



5.8 Receiver Switching Characteristics

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT	
t _{PLH}	Propagation delay time, low-to-high-level output 1/2 UL	HVD05			14.6	25	ns
t _{PHL}	Propagation delay time, high-to-low-level output 1/2 UL	HVD05	=		14.6	25	ns
	Drangation delay time law to high level output 1/0 LII	HVD06	-		55	70	
t _{PLH}	Propagation delay time, low-to-high-level output 1/8 UL	HVD07	_		55	70	ns
	Description delevations bink to level out to 4/0 III	HVD06	-		55	70	
t _{PHL}	Propagation delay time, high-to-low-level output 1/8 UL	HVD07	$V_{ID} = -1.5 \text{ V to } 1.5 \text{ V},$		55	70	ns
		HVD05	C _L = 15 pF, See Figure 6-8			2	
t _{sk(p)}	Pulse skew (t _{PHL} - t _{PLH})	HVD06				4.5	ns
		HVD07	-			4.5	
		HVD05				6.5	
t _{sk(pp)} (2)	Part-to-part skew	HVD06	-			14	ns
		HVD07	-			14	
t _r	Output signal rise time		C _L = 15 pF,		2	3	
t _f	Output signal fall time		See Figure 6-8		2	3	ns
t _{PZH1}	Output enable time to high level					10	
t _{PZL1}	Output enable time to low level		$C_L = 15 \text{ pF},$			10	
t _{PHZ}	Outroot dischile time from high level		DE at 3 V, See Figure 6-9	,		15	ns
t _{PLZ}						15	
t _{PZH2}	Propagation delay time, standby-to-high-level output		C _L = 15 pF, DE at 0,			6	
t _{PZL2}	Propagation delay time, standby-to-low-level output		See Figure 6-10			6	μs

⁽¹⁾ All typical values are at 25°C and with a 5-V supply.

⁽²⁾ $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.



5.9 Typical Characteristics

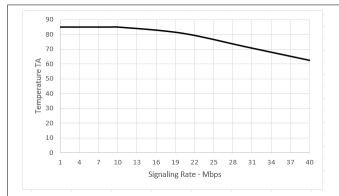


Figure 5-1. HVD05 Maximum Recommended Still-Air Operating Temperature vs Signaling Rate (D-Package)

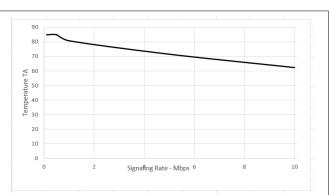


Figure 5-2. HVD06 Maximum Recommended Still-Air Operating Temperature vs Signaling Rate (D-Package)

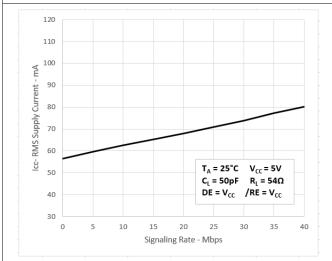


Figure 5-3. HVD05 RMS Supply Current vs Signaling Rate

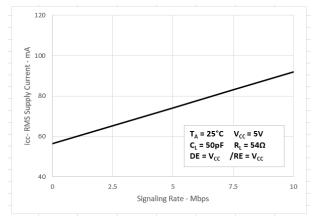
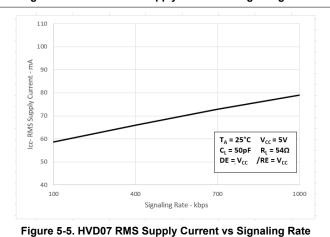
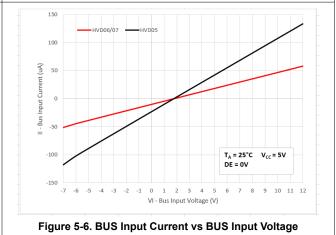


Figure 5-4. HVD06 RMS Supply Current vs Signaling Rate







5.9 Typical Characteristics (continued)

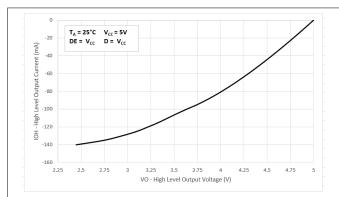


Figure 5-7. Driver High-Level Output Current vs High-Level Output Voltage

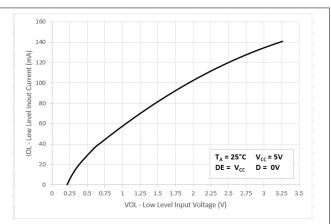


Figure 5-8. Driver Low-Level Output Current vs Low-Level Output Voltage

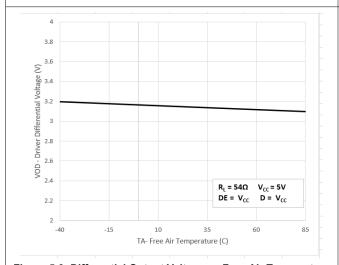


Figure 5-9. Differential Output Voltage vs Free-Air Temperature

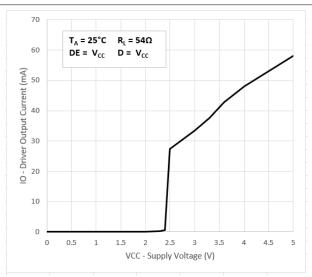


Figure 5-10. Driver Output Current vs Supply Voltage

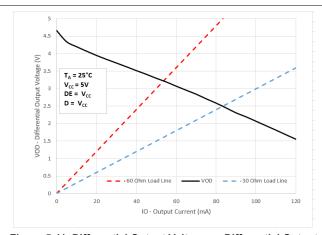


Figure 5-11. Differential Output Voltage vs Differential Output Current

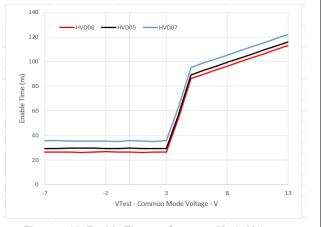


Figure 5-12. Enable Time vs Common-Mode Voltage (See Figure 5-13)



5.9 Typical Characteristics (continued)

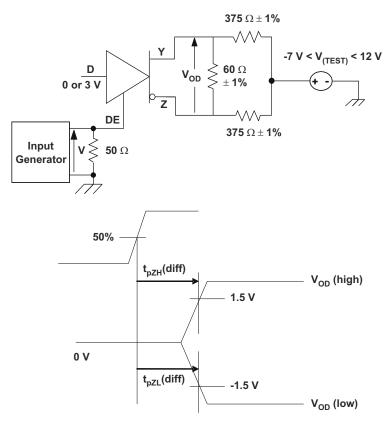


Figure 5-13. Driver Enable Time From DE to ${\rm V}_{\rm OD}$



Parameter Measurement Information

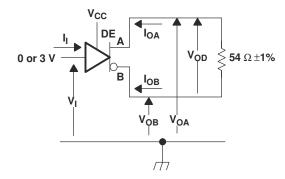


Figure 6-1. Driver V_{OD} Test Circuit and Voltage and Current Definitions

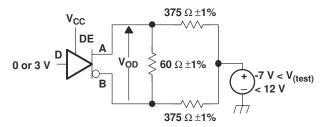


Figure 6-2. Driver V_{OD} With Common-Mode Loading Test Circuit

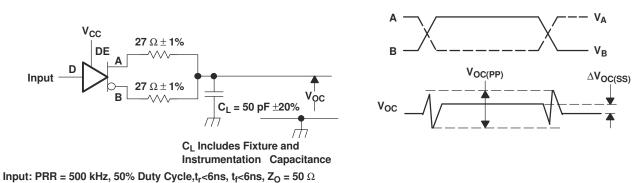


Figure 6-3. Test Circuit and Definitions for the Driver Common-Mode Output Voltage

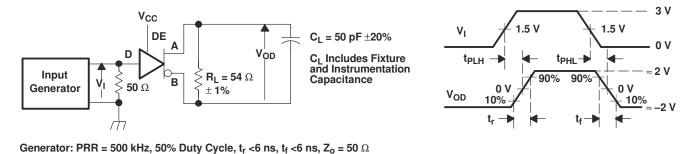
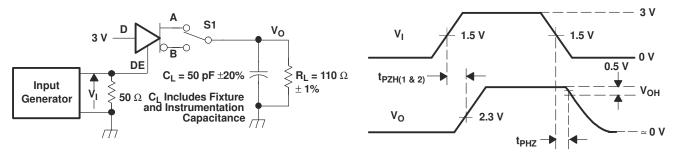


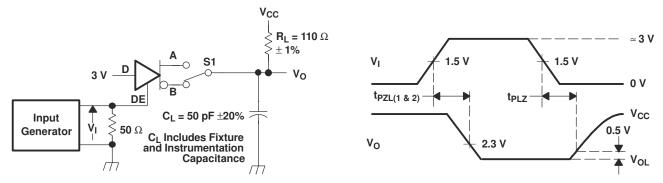
Figure 6-4. Driver Switching Test Circuit and Voltage Waveforms





Generator: PRR = 100 kHz, 50% Duty Cycle, t_r <6 ns, t_f <6 ns, Z_{O} = 50 Ω

Figure 6-5. Driver High-Level Enable and Disable Time Test Circuit and Voltage Waveforms



Generator: PRR = 100 kHz, 50% Duty Cycle, t_r <6 ns, t_f <6 ns, Z_o = 50 Ω

Figure 6-6. Driver Low-Level Output Enable and Disable Time Test Circuit and Voltage Waveforms

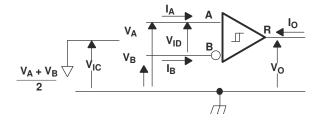


Figure 6-7. Receiver Voltage and Current Definitions

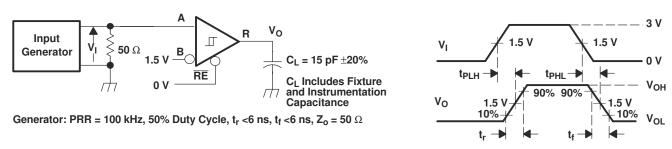


Figure 6-8. Receiver Switching Test Circuit and Voltage Waveforms



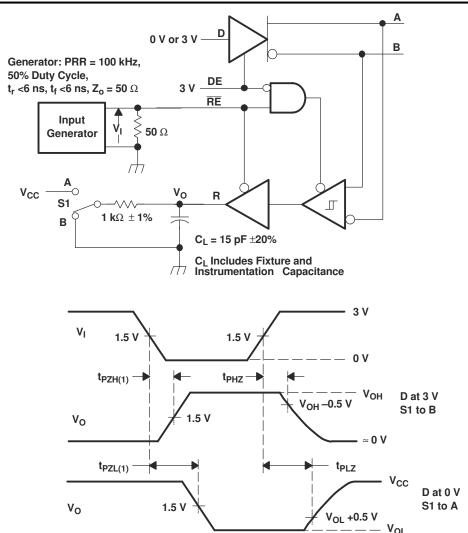
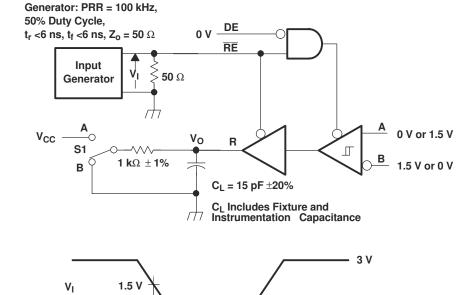


Figure 6-9. Receiver Enable and Disable Time Test Circuit and Voltage Waveforms With Drivers Enabled





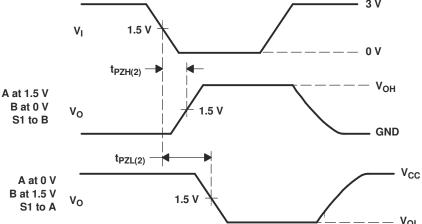
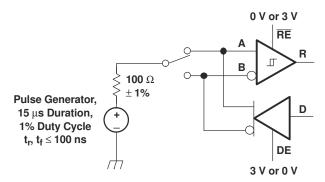


Figure 6-10. Receiver Enable Time From Standby (Driver Disabled)



NOTE: This test is conducted to test survivability only. Data stability at the R output is not specified.

Figure 6-11. Test Circuit, Transient Over Voltage Test

6 Function Tables

Table 6-1. DRIVER

INPUT	ENABLE	OUTPUTS	
D	DE	Α	В
Н	Н	Н	L
L	Н	L	Н
X	L	Z	Z
Open	Н	H	L
X	Open	Z	Z

Table 6-2. RECEIVER

DIFFERENTIAL INPUTS(1)	ENABLE	OUTPUT
$V_{ID} = V_A - V_B$	RE	R
V _{ID} ≤ −0.2 V	L	L
$-0.2 \text{ V} < \text{V}_{\text{ID}} < -0.01 \text{ V}$	L	?
-0.01 V≤ V _{ID}	L	Н
X	Н	Z
Open Circuit	L	Н
Short Circuit	L	Н
IDLE Bus	L	Н
X	Open	Z

⁽¹⁾ H = high level; L = low level; Z = high impedance; X = irrelevant;? = indeterminate

6.1 Receiver Failsafe

The differential receiver is "failsafe" to invalid bus states caused by:

- open bus conditions such as a disconnected connector,
- shorted bus conditions such as cable damage shorting the twisted-pair together, or
- idle bus conditions that occur when no driver on the bus is actively driving

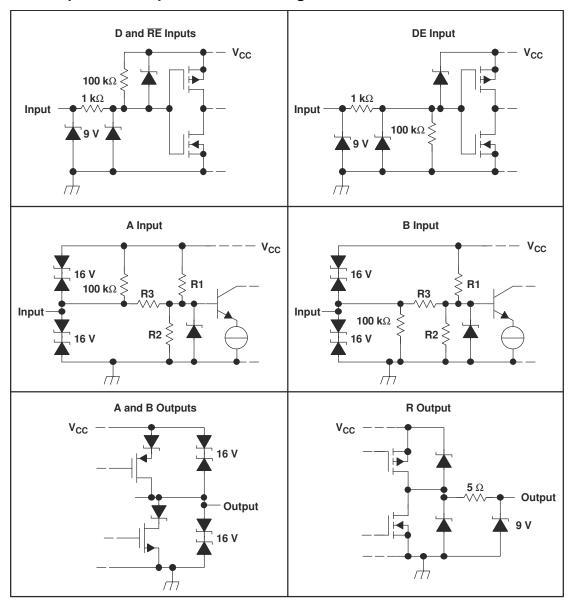
In any of these cases, the differential receiver outputs a failsafe logic High state, so that the output of the receiver is not indeterminate.

Receiver failsafe is accomplished by offsetting the receiver thresholds so that the "input indeterminate" range does not include zero volts differential. To comply with the RS-422 and RS-485 standards, the receiver output must output a High when the differential input V_{ID} is more positive than +200 mV, and must output a Low when the V_{ID} is more negative than -200 mV. The receiver parameters which determine the failsafe performance are V_{IT+} and V_{IT-} and V_{HYS} . As seen in the Receiver Electrical Characteristics table, differential signals more negative than -200 mV will always cause a Low receiver output. Similarly, differential signals more positive than +200 mV will always cause a High receiver output.

When the differential input signal is close to zero, it will still be above the V_{IT+} threshold, and the receiver output is High. Only when the differential input is more negative than V_{IT-} will the receiver output transition to a Low state. So, the noise immunity of the receiver inputs during a bus fault condition includes the receiver hysteresis value V_{HYS} (the separation between V_{IT+} and V_{IT-}) as well as the value of V_{IT+} .



7 Equivalent Input and Output Schematic Diagrams



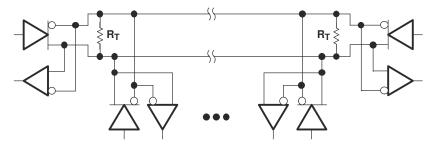
	R1/R2	R3
SN65HVD05	9 k Ω	45 k Ω
SN65HVD06	36 k Ω	180 k Ω
SN65HVD07	36 k Ω	180 k Ω

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

Typical Application



Device	Number of Devices on Bus
HVD05	64
HVD06	256
HVD07	256

NOTE: The line should be terminated at both ends with its characteristic impedance $(R_T = Z_O)$. Stub lengths off the main line should be kept as short as possible.

Figure 8-1. Typical Application Circuit



9 Device and Documentation Support

9.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

9.3 Trademarks

TI E2E[™] is a trademark of Texas Instruments.

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9.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN65HVD05D	NRND	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VP05	
SN65HVD05DR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VP05	Samples
SN65HVD05P	ACTIVE	PDIP	Р	8	50	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	65HVD05	Samples
SN65HVD06D	NRND	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VP06	
SN65HVD06DG4	NRND	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VP06	
SN65HVD06DR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VP06	Samples
SN65HVD07D	NRND	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VP07	
SN65HVD07DR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VP07	Samples
SN65HVD07P	ACTIVE	PDIP	Р	8	50	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	65HVD07	Samples
SN75HVD05D	NRND	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	VN05	
SN75HVD05P	NRND	PDIP	Р	8	50	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	75HVD05	
SN75HVD06D	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	VN06	Samples
SN75HVD06DR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	VN06	Samples
SN75HVD07D	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	VN07	Samples
SN75HVD07DR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	VN07	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".



PACKAGE OPTION ADDENDUM

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Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65HVD05DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65HVD06DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65HVD07DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN75HVD06DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN75HVD07DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1



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*All dimensions are nominal

7 III GIII I GII I GII GII GII GII GII G							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65HVD05DR	SOIC	D	8	2500	356.0	356.0	35.0
SN65HVD06DR	SOIC	D	8	2500	356.0	356.0	35.0
SN65HVD07DR	SOIC	D	8	2500	356.0	356.0	35.0
SN75HVD06DR	SOIC	D	8	2500	340.5	336.1	25.0
SN75HVD07DR	SOIC	D	8	2500	340.5	336.1	25.0

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN65HVD05D	D	SOIC	8	75	507	8	3940	4.32
SN65HVD05P	Р	PDIP	8	50	506	13.97	11230	4.32
SN65HVD06D	D	SOIC	8	75	507	8	3940	4.32
SN65HVD06DG4	D	SOIC	8	75	507	8	3940	4.32
SN65HVD07D	D	SOIC	8	75	507	8	3940	4.32
SN65HVD07P	Р	PDIP	8	50	506	13.97	11230	4.32
SN75HVD05D	D	SOIC	8	75	507	8	3940	4.32
SN75HVD05P	Р	PDIP	8	50	506	13.97	11230	4.32
SN75HVD06D	D	SOIC	8	75	507	8	3940	4.32
SN75HVD07D	D	SOIC	8	75	507	8	3940	4.32



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



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